(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

G00002

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
7 March 2002 (07.03.2002)

PCT

(10) International Publication Number
WO 02/019409 A3

(51) International Patent Classification[7]: H01L 21/311, 21/306

(21) International Application Number: PCT/US01/26833

(22) International Filing Date: 29 August 2001 (29.08.2001)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09/653,554 31 August 2000 (31.08.2000) US

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(81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PH, PL, PT, RO, RU, SD, SE, SG, SI, SK, SL, TJ, TM, TR, TT, TZ, UA, UG, UZ, VN, YU, ZA, ZW.

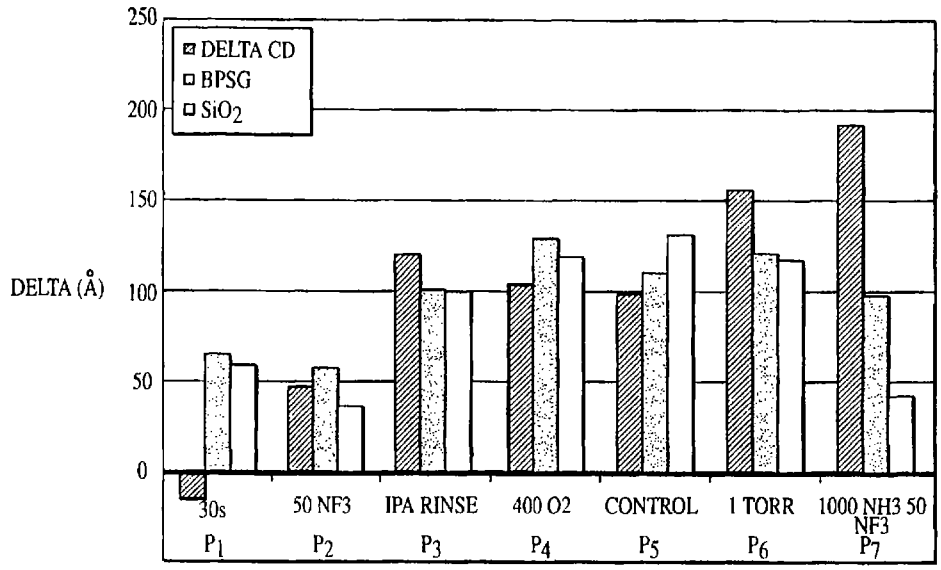
(84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:
— with international search report
— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

[Continued on next page]

162162

(54) Title: METHOD FOR SELECTIVE ETCHING OF OXIDES



FUSION DRY CLEAN CD TEST

(57) Abstract: An improved dry plasma cleaning process for the removal of native oxides, or other oxide films or growth residue, from openings formed in an insulating layer provided over a semiconductor substrate, without damaging the substrate or significantly affecting the critical dimension of the opening is disclosed. A mixture of nitrogen trifluoride (NF_3), ammonia (NH_3) and oxygen (O_2) is first injected upstream into a microwave plasma source and is exited, and then the plasma is flowed downstream from the plasma source into a reaction chamber containing the substrate.

WO 02/019409 A3

(88) Date of publication of the international search report:
25 July 2002

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.